

Development of Target Ion Source Systems for radioactive beams at GANIL

□Spiral 1 upgrade

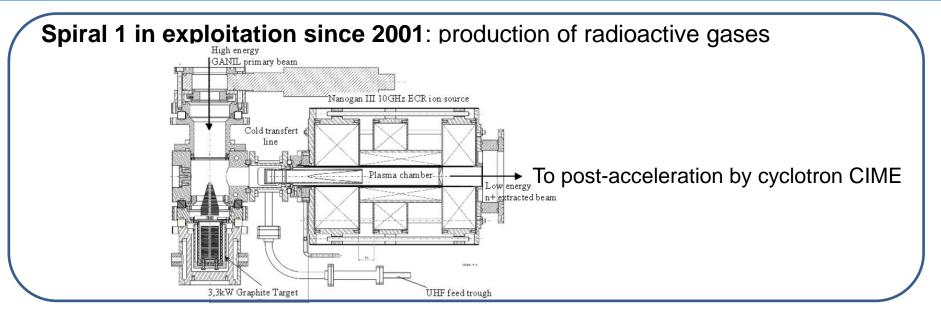
➤A new TISS using a Febiad ion source

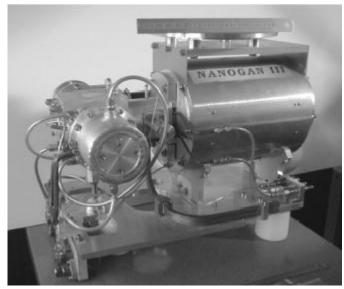
□Spiral 2 phase 2

The oven for the UCx target
The ECR ion source
The Laser ion source

The Laser ion source







The Spiral 1 Target Ion Source System



Production target for Ne, Ar, Kr, N, O and F isotopes



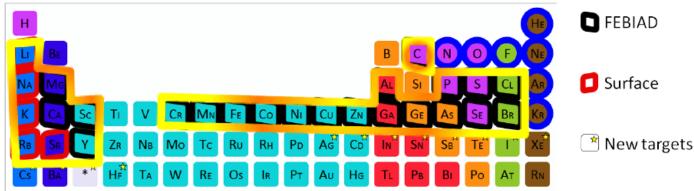
Production and diffusion target for He

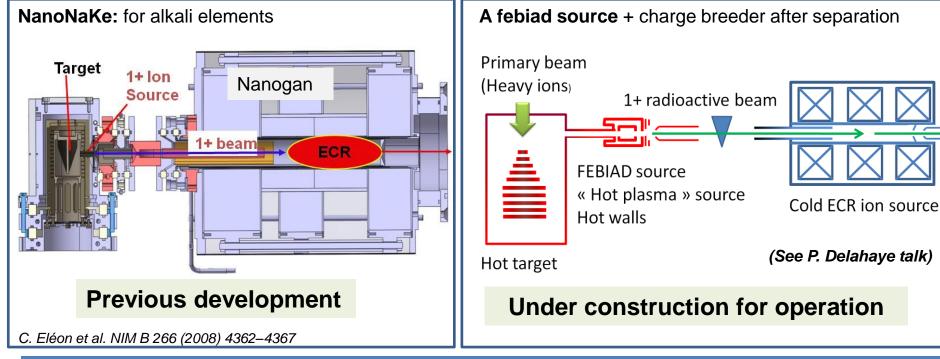
A.C.C. Villari et al. Nuclear Physics A 787 (2007)



1- Spiral 1 upgrade

To extend the range of radioactive beams



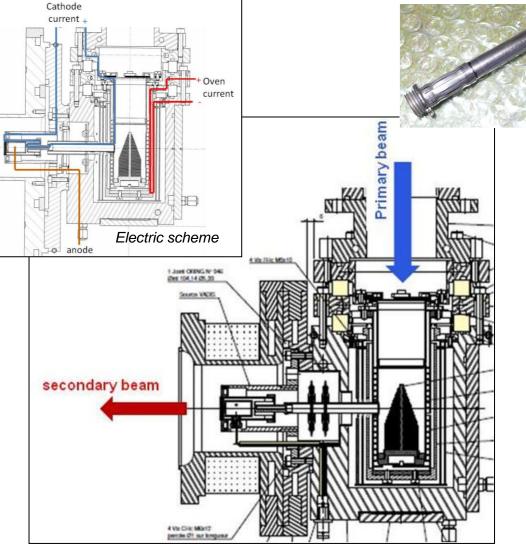




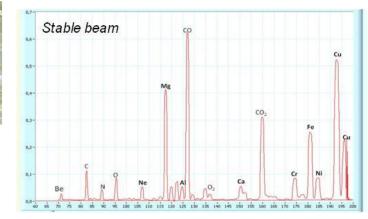
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A first prototype of a Febiad ion source tested on line

The VADIS (supplied by CERN) is connected to the Spiral C target in a Ta container .



Encouraging results but reliability has to be improved



TISS has worked for several days

Isotope	Half life	Primary beam	Power (W)	Measured 1+ intensity	
38K	6.3min	58Ni	4	3.80E+04	
38mK	923ms	58Ni	4	1220	
53Fe	8.51 min	58Ni	34	6.60E+04	
53mFe	2.526min	58Ni	34	1.40E+04	
58Cu	3.204s	58Ni	37	4.30E+03	
58Mn	3s	58Ni	37	5.70E+04	
59Cu	81.5s	58Ni	38	7.30E+04	



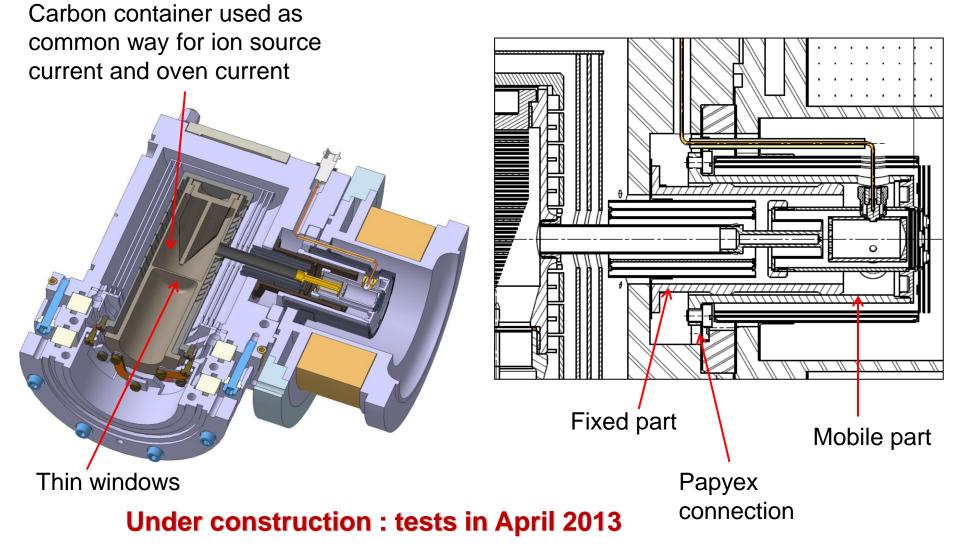
Olivier BAJEAT

EMIS 2012



New prototype design

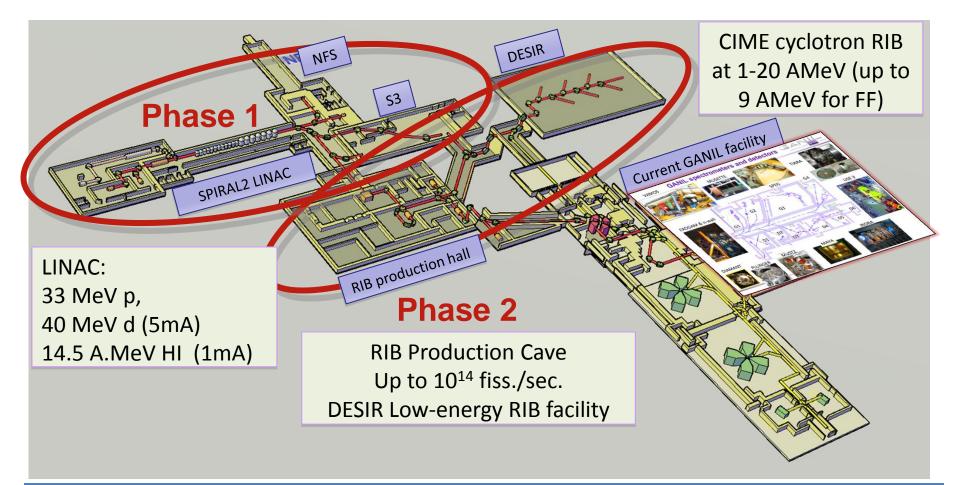
The ion source is now mobile in the direction of secondary beam :





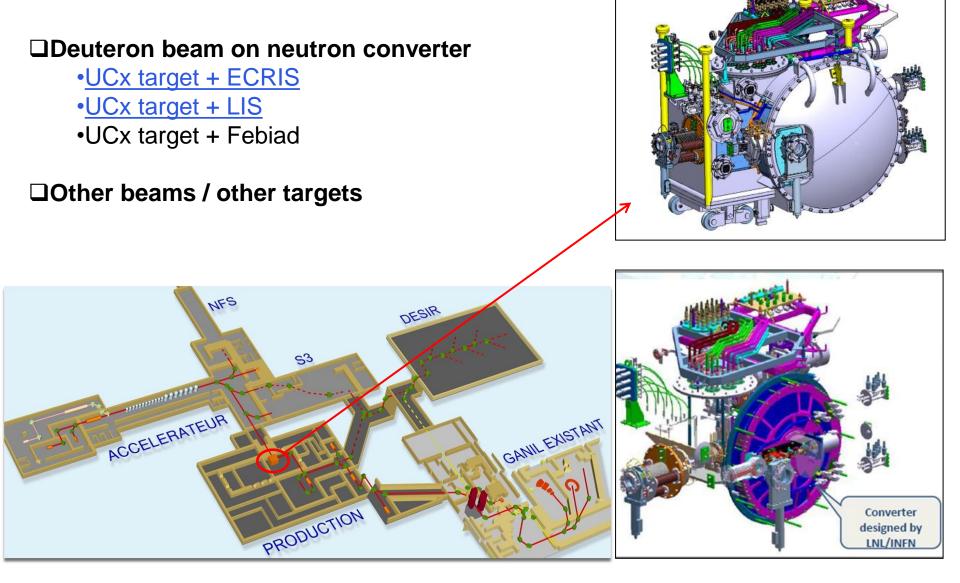
2- Spiral 2 phase 2

Phase 1: High intensity stable beams + Experimental rooms (S³ + NFS) (First beam Sept 2014) **Phase 2**: High-intensity low-energy (DESIR) & post-accelerated Radioactive Ion Beam facility





The production module





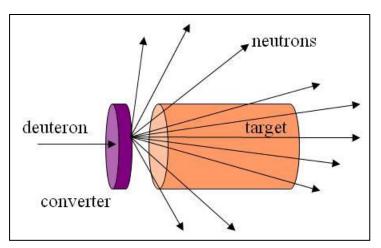
The UCx target

•Designed to produce up to 5.10¹³ fission/s with 5 mA / 40 MeV deuteron on carbon converter.

•Coupled with ECRIS, LIS or Febiad ion source

- •For good diffusion/effusion the target has to be maintained at 2000°C
- •Must work during 3 months

•The reference target (\emptyset 80; L 80) is constituted of 19 series of uranium carbide (UCx) disks (\emptyset 15; thickness 1mm).



For optimized production, the converter must be as close as possible to the target.

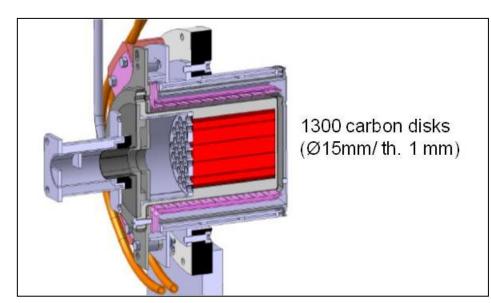


Reference target : L 80 mm / Ø 80 mm. For the oven development UCx is replaced by carbon

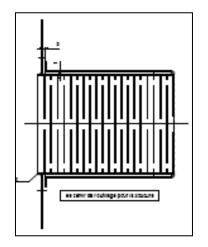


A first oven prototype in tantalum

•Choice of tantalum because of the specification of long duration at 2000°C







Thickness 0,1 mm with slits; surrounded by 2 tantalum screens 750 A / 11,8 V (8800 W) \rightarrow 1500°C in the target

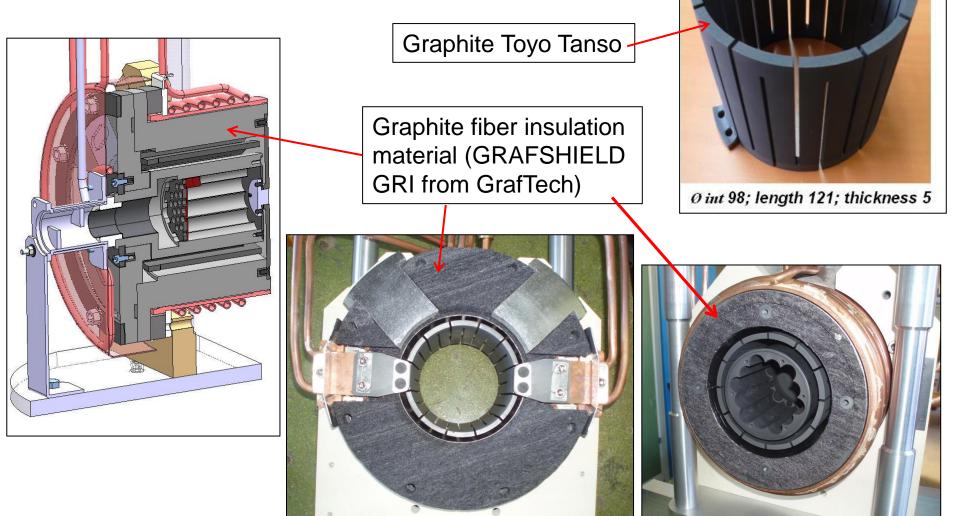
This prototype has been used during several months up to **1500°C** with a ECRIS.



Spiral 2: the oven for the UCx target

A prototype in carbon

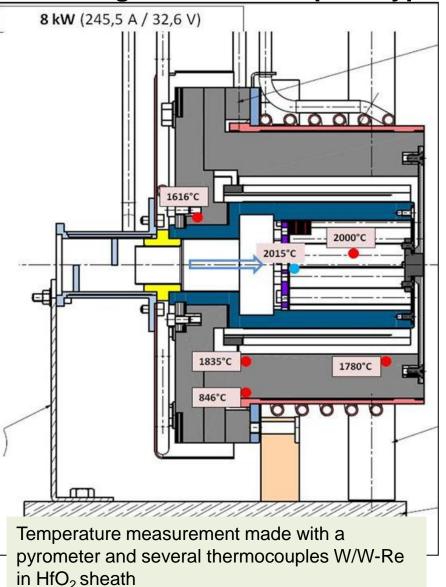
- •Easier than Tantalum to reach more than 2000°C
- •Lifetime lower due to high evaporation rate of carbon





Spiral 2: the oven for the UCx target

1st heating of the carbon prototype



•Failure after about 13 days at T > 2000°C with many interruptions.



Resistance failure





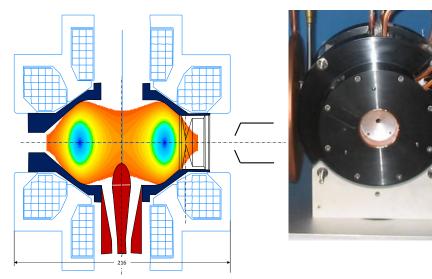
Some contact has caused local over-heating

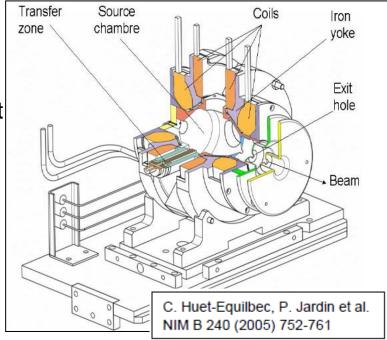


ECR ion source 2.45 GHz

 \rightarrow used for gaseous elements

- Symmetry of revolution
- Cooled chamber in stainless steel
- Magnetic confinement by the coils (no permanent magnet)
- Injection of the RF with an antenna
 Radiation hard (only mineral and metallic materials)





	Не	Ne	Ar	Kr	Xe
ε _{ion} 1+ (%)	7	35	52	55	67

1+ ionization efficiencies (data from A. Pichard thesis - Université de Caen - 26/11/2010)

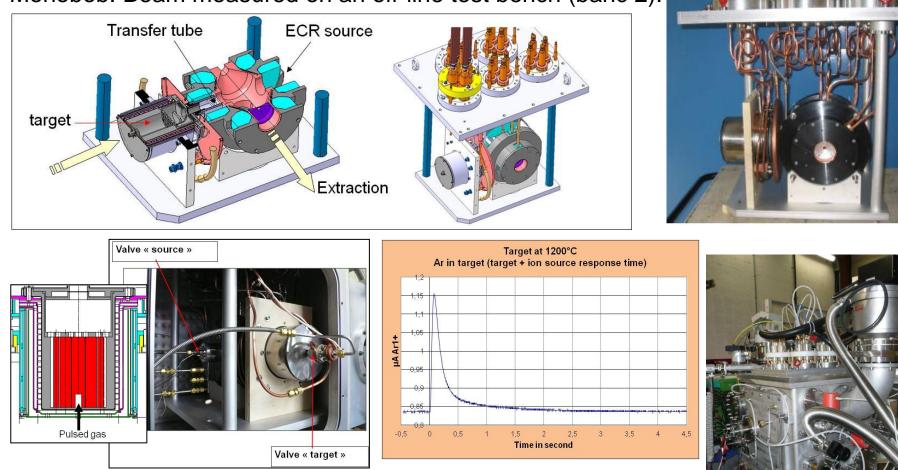
Magnetic confinement in the source

Current extracted from the source < 1 mA



Spiral 2: the ECRIS coupled with a target

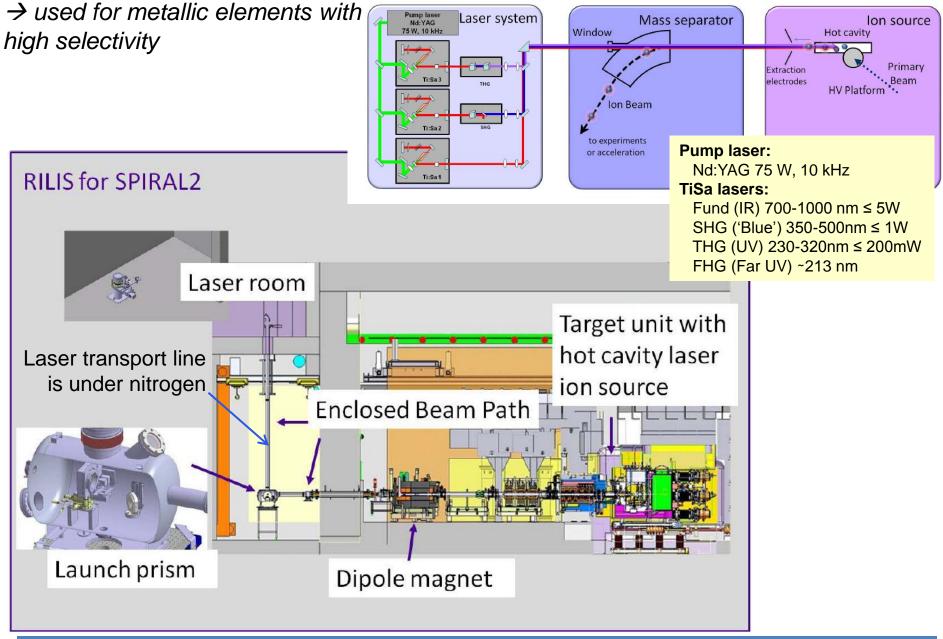
1st prototype oven (Ta) heated up to 1500°C coupled with Monobob. Beam measured on an off-line test bench (banc 2).



 Functioning of the TISS in a box similar to the production module and experience feedback for Spiral 2
 Effusion measurement for rare gazes



Spiral 2: the laser ion source

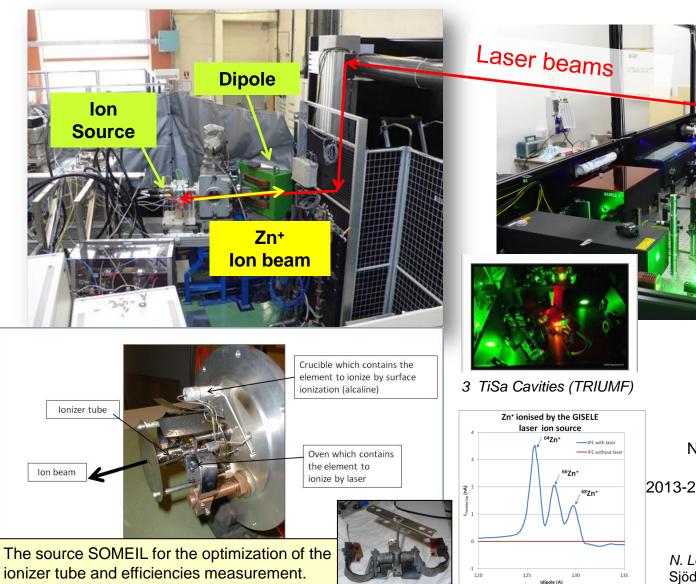




Laser Ion Source

Spiral 2: the laser ion source

<u>GANIL Ion Source using Electron Laser Excitation</u> ANR 2009-2013, 510k€, GANIL-IPNO-Mainz Univ



JOHANNES GUTENBERG UNIVERSITÄT MAIN

LISELE

2 Frequency Conversion Cavities (Mainz Univ)

July 2011:1st Ga+ beam

Nov 2012: Scheme dvt of Zn+

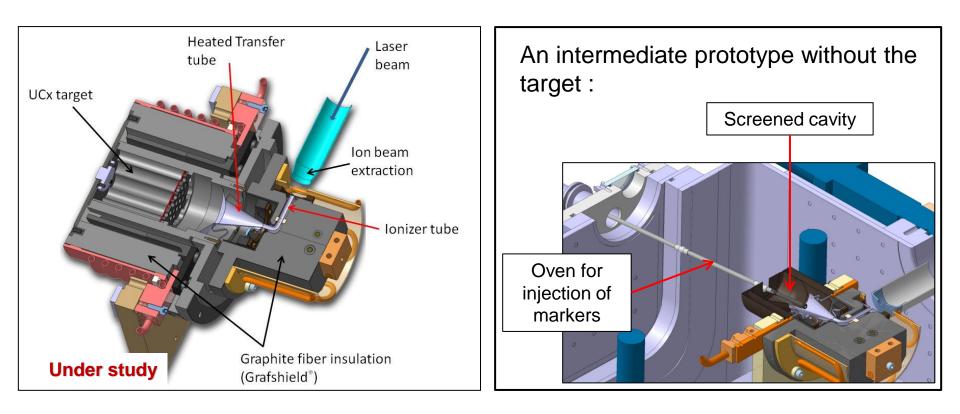
2013-2014: <u>Sn, In, Y (</u>Day1 SPIRAL2 φ2)

N. Lecesne et al. RSI 81, 02A910 2010 Sjödin et al, Hyperfine Interaction, accepted



The laser TISS for Spiral 2

- •UCx target heated up to 2000°C
- •Elements to ionize by Laser : Ga, Zn, Sn, In, Y...
- •All the surfaces could be maintained at 1500-2000°C.
- •The transfer tube and the ionizer tube are heated independently \rightarrow polarities could be reversed to slow down the radioactive ions produced in the transfer tube by surface ionization.





MAM

LIEBHERR

Thank you for your attention !

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4 Octobre 2012 GANIL-SPIRAL2

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